

A1
cont.
2. (Amended) An arrangement as claimed in claim 1, wherein the active material comprises erbium-doped glass, operative to emit radiation at 1.54 μm when optically pumped.

3. (Amended) An arrangement as claimed in claim 1, wherein the length of the chip of active material, in the propagation direction of the laser light, is smaller than about 5 mm.

4. (Amended) An arrangement as claimed in claim 1, wherein the length of the chip of optically bleachable material, in the propagation direction of the laser light, is smaller than about 5 mm.

A2
6. (Amended) An arrangement as claimed in claim 5, wherein the laser diode emits light in a wavelength range between 940 nm and 1000 nm.

7. (Amended) An arrangement as claimed in claim 6, wherein the laser diode is a InGaAs diode emitting light at 970 nm.

A3
14. (New) An arrangement as claimed in claim 1, wherein the length of the chip of active material, in the propagation direction of the laser light, is smaller than about 1 mm.

15. (New) An arrangement as claimed in claim 1, wherein the length of the chip of optically bleachable material, in the propagation direction of the laser light, is smaller than about 1 mm.

16. (New) An arrangement as claimed in claim 5, wherein the pump diode laser is a continuous-wave diode laser.

A3
cont.

17. (New) An arrangement as claimed in claim 16, wherein the pump diode laser has an output power of less than 1 Watt.
